# **BGU7052**

# SiGe:C Low Noise High Linearity Amplifier

Rev. 2 — 21 February 2012

**Product data sheet** 

# 1. Product profile

### 1.1 General description

The BGU7052 is a low noise high linearity amplifier for wireless infrastructure applications. The LNA has a high input and output return loss and is designed to operate between 1.5 GHz and 2.5 GHz. It is housed in a  $3 \times 3 \times 0.85$  mm<sup>3</sup> 10-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

### 1.2 Features and benefits

- Low Noise Figure (NF) = 0.76 dB at 1900 MHz
- High linearity performance, IP3<sub>O</sub> = 35 dBm at 1900 MHz
- High input and output return loss
- Unconditionally stable
- 110 GHz transit frequency SiGe:C technology
- Supply voltage 3.3 V
- Small 10-terminal leadless package 3 × 3 × 0.85 mm<sup>3</sup>
- Moisture sensitivity level 1

### 1.3 Applications

- LNA for wireless infrastructure applications (1.5 GHz to 2.5 GHz)
- Low noise applications

#### 1.4 Quick reference data

Table 1. Quick reference data

f = 1900 MHz;  $T_{amb}$  = 25 °C; input and output 50  $\Omega$ ; unless otherwise specified.

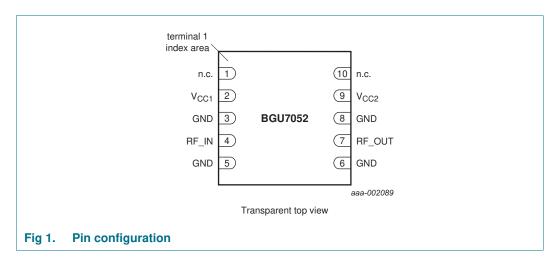
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		3.0	3.3	3.6	V
I <sub>CC</sub>	supply current		63	80	95	mΑ
G <sub>ass</sub>	associated gain		18.5	20	21.5	dB
NF	noise figure		-	0.76	0.95	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		13	14.5	-	dBm
IP3 <sub>O</sub>	output third-order intercept point		32	35	-	dBm



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# 2. Pinning information

### 2.1 Pinning



### 2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
n.c.	1, 10	not connected
GND	3, 5, 6, 8	ground
RF_IN	4	RF input
RF_OUT	7	RF output
V <sub>CC</sub>	2, 9	supply voltage

# 3. Ordering information

Table 3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
BGU7052	HVSON10	plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body 3 x 3 x 0.85 mm	SOT650-1				

### **SiGe:C Low Noise High Linearity Amplifier**

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0	5	V
P <sub>tot</sub>	total power dissipation		-	300	mW
$P_{i(RF)CW} \\$	continuous waveform RF input power	$V_{CC} = 3.3 \text{ V}$	-	20	dBm
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-40	+85	°C
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	-	4	kV
		Charged Device Model (CDM); According JEDEC standard 22-C101B	-	2	kV

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		20	K/W

### 6. Characteristics

#### Table 6. Characteristics

 $V_{CC}$  = 3.3 V;  $T_{amb}$  = 25 °C; input and output 50  $\Omega$ ; unless otherwise specified. All RF parameters are measured at the device RF in and RF output terminals.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CC}$	supply current		63	80	95	mA
$G_{ass}$	associated gain	f = 1750 MHz	-	21.5	-	dB
		f = 1900 MHz	18.5	20	21.5	dB
		f = 1950 MHz	-	19.7	-	dB
NF	noise figure	f = 1750 MHz	-	0.76	-	dB
		f = 1900 MHz	-	0.76	0.95	dB
		f = 1950 MHz	-	0.79	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 1750 MHz	-	15.5	-	dBm
		f = 1900 MHz	13	14.5	-	dBm
		f = 1950 MHz	-	14.5	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 1750 MHz	-	36.8	-	dBm
		f = 1900 MHz	32	35.3	-	dBm
		f = 1950 MHz	-	35.1	-	dBm

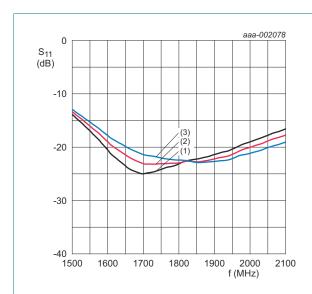
### SiGe:C Low Noise High Linearity Amplifier

 Table 6.
 Characteristics ...continued

 $V_{CC}$  = 3.3 V;  $T_{amb}$  = 25 °C; input and output 50  $\Omega$ ; unless otherwise specified. All RF parameters are measured at the device RF in and RF output terminals.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
RL <sub>in</sub> ir	input return loss	f = 1750 MHz	-	23	-	dB
		f = 1900 MHz	-	23	-	dB
		f = 1950 MHz	-	22	-	dB
RL <sub>out</sub>	output return loss	f = 1750 MHz	-	22	-	dB
		f = 1900 MHz	-	22	-	dB
		f = 1950 MHz	-	21	-	dB
ISL	isolation	f = 1750 MHz	-	28.5	-	dB
		f = 1900 MHz	-	27.5	-	dB
		f = 1950 MHz	-	27	-	dB
K	Rollett stability factor	$0~GHz \leq f \leq 25~GHz$	1	-	-	

### 6.1 Performance curves



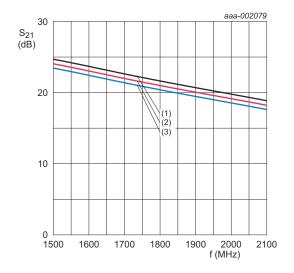
 $V_{CC} = 3.3 \text{ V}.$ 

(1) 
$$T_i = -40 \, ^{\circ}C$$

(2) 
$$T_i = 25 \,^{\circ}C$$

(3)  $T_j = 85 \,^{\circ}C$ 

Fig 2. Input reflection coefficient as a function of frequency



 $V_{CC} = 3.3 \text{ V}.$ 

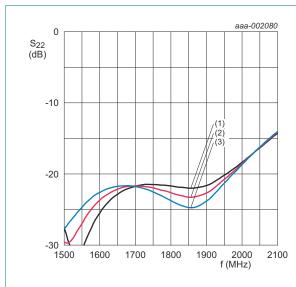
(1) 
$$T_i = -40 \, ^{\circ}C$$

(2) 
$$T_j = 25 \, ^{\circ}C$$

(3)  $T_i = 85 \,^{\circ}C$ 

Fig 3. Forward transmission coefficient as a function of frequency

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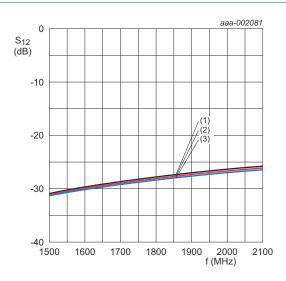
 $V_{CC} = 3.3 \text{ V}.$ 

(1) 
$$T_i = -40 \, ^{\circ}C$$

(2) 
$$T_i = 25 \, ^{\circ}C$$

(3)  $T_i = 85 \, ^{\circ}C$ 

Fig 4. Output reflection coefficient as a function of frequency



 $V_{CC} = 3.3 \text{ V}.$ 

(1) 
$$T_i = -40 \, ^{\circ}C$$

(2) 
$$T_j = 25 \, ^{\circ}C$$

(3)  $T_i = 85 \, ^{\circ}C$ 

Fig 5. Reverse transmission coefficient as a function of frequency

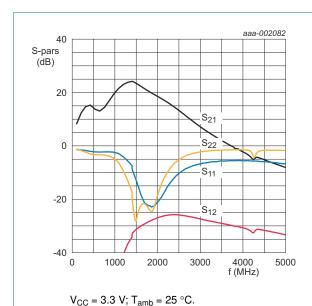
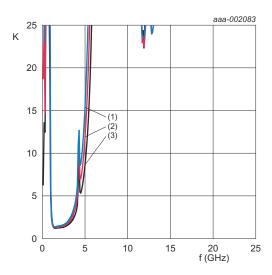


Fig 6. Wideband s-parameters as a function of frequency



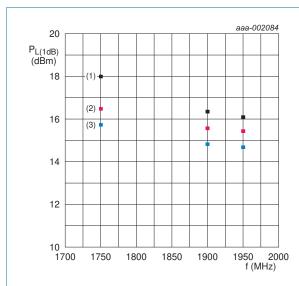
 $V_{CC} = 3.3 \text{ V}.$ 

(1) 
$$T_i = -40 \, ^{\circ}C$$

(3)  $T_j = 85 \, ^{\circ}C$ 

Fig 7. Stability K-factor as a function of frequency

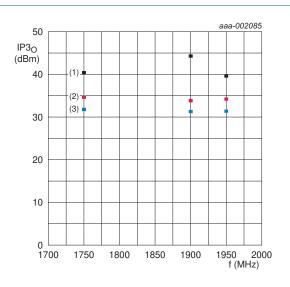
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$$V_{CC} = 3.3 \text{ V}.$$

- (1)  $T_i = -40 \, ^{\circ}C$
- (2)  $T_j = 25 \,^{\circ}C$
- (3)  $T_i = 85 \, ^{\circ}C$

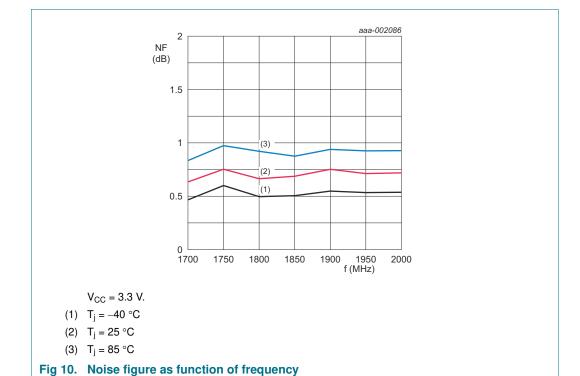
Fig 8. Output power at 1 dB gain compression as a function of frequency



$$V_{CC} = 3.3 \text{ V}.$$

- (1)  $T_i = -40 \, ^{\circ}\text{C}$
- (2)  $T_j = 25$  °C
- (3)  $T_i = 85 \, ^{\circ}C$

Fig 9. Output third-order intercept point as a function of frequency

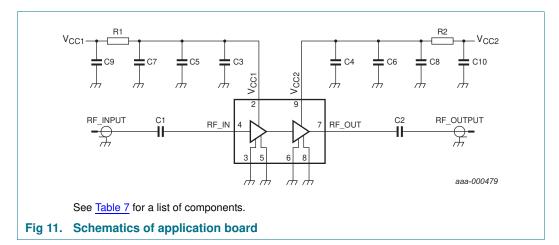


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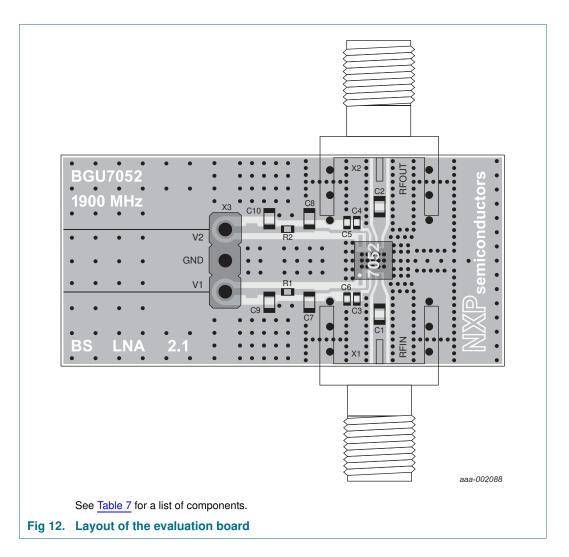
# 7. Application information

<u>Figure 11</u> shows the typical application circuit for the BGU7052. The device is internally matched to 50  $\Omega$ , and therefore does not need any external matching. The value of the input and output DC blocking C1 and C2 are recommended to be 1 nF. DC decoupling capacitors C3 and C4 should be located as close as possible to the BGU7052.

In case different system blocks are supplied via the same voltage rail, it is recommended to use a bias choke in the bias line on the positions of R1 and R2. The value of this choke is depending on the frequency that needs to be dececoupled.



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**Table 7.** List of components See Figure 11 for schematics.

Component	Description		Value	Size	Function
C1, C2	capacitor	[1]	1 nF	0402	DC block
C3, C4	capacitor	[1]	100 pF	0402	bias decoupling
C5, C6	capacitor	[1]	100 nF	0402	bias decoupling
C7, C8, C9, C10	capacitor	[2]	100 nF	0603	optional
R1, R2	resistor		0 Ω	0402	

<sup>[1]</sup> Murata GRM155 or capacitor of same quality.

<sup>[2]</sup> Murata GRM188 or capacitor of same quality.

## SiGe:C Low Noise High Linearity Amplifier

# 8. Package outline

HVSON10: plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body  $3 \times 3 \times 0.85$  mm

SOT650-1

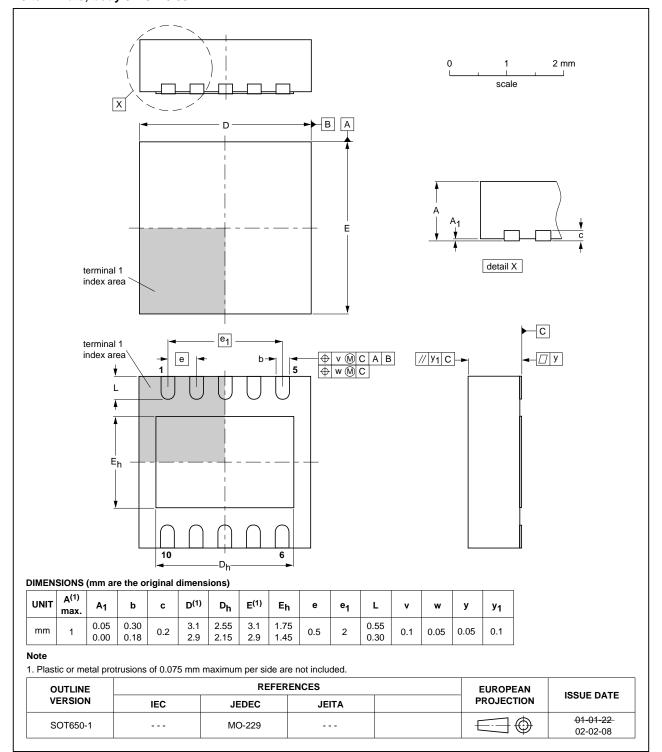


Fig 13. Package outline SOT650-1 (HVSON10)

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# SiGe:C Low Noise High Linearity Amplifier

# 9. Abbreviations

Table 8. Abbreviations

Acronym	Description
AC	Alternating Current
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LNA	Low Noise Amplifier
PDA	Personal Digital Assistant
RF	Radio Frequency
SiGe:C	Silicon Germanium Carbon

# 10. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU7052 v.2	20120221	Product data sheet	-	BGU7052 v.1
Modifications:	• <u>Table 6</u> : upda	ated		
BGU7052 v.1	20120214	Product data sheet	-	-

### SiGe:C Low Noise High Linearity Amplifier

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Product data sheet

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